

## NTE2328 (NPN) & NTE2329 (PNP) Silicon Complementary Transistors Audio Power Output

### Features:

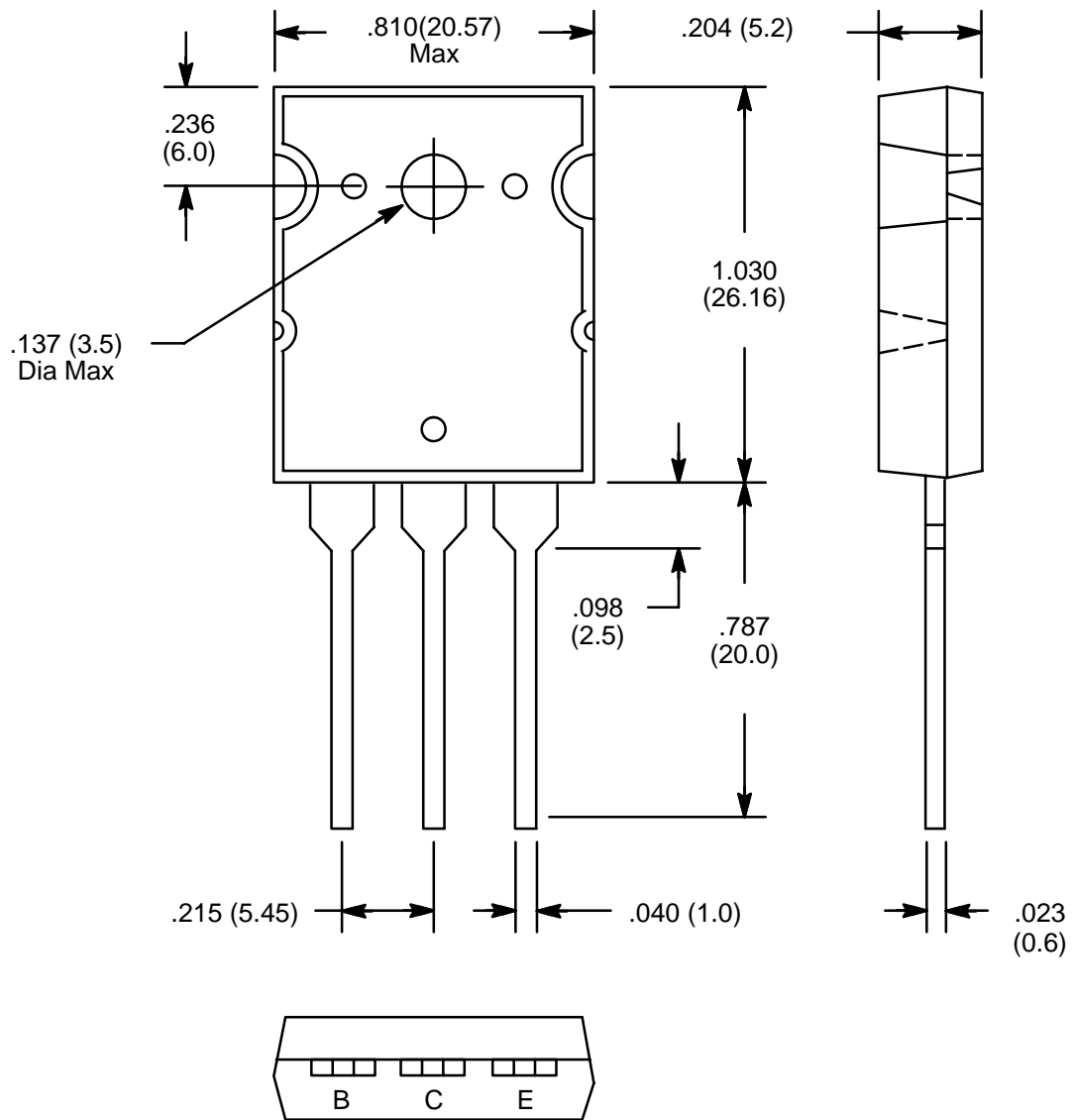
- Recommended for 100W High Fidelity Audio Frequency Amplifier Output Stage

### Absolute Maximum Ratings: ( $T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	200V
Collector–Emitter Voltage, $V_{CEO}$ .....	200V
Emitter–Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$ .....	15A
Base Current, $I_B$ .....	1.5A
Collector Power Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$ .....	150W
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C

### Electrical Characteristics: ( $T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 200V, I_E = 0$	–	–	5.0	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{BE} = 5V, I_C = 0$	–	–	5.0	$\mu\text{A}$
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50\text{mA}, I_B = 0$	200	–	–	V
DC Current Gain	$h_{FE1}$	$V_{CE} = 5V, I_C = 1A$	55	–	160	
	$h_{FE2}$	$V_{CE} = 5V, I_C = 8A$	35	60	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10A, I_B = 1A$	–	1.5	3.0	V
Base–Emitter Voltage	$V_{BE}$	$V_{CE} = 5V, I_C = 8A$	–	1.0	1.5	V
Transistion Frequency	$f_T$	$V_{CE} = 5V, I_C = 1A$	–	25	–	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1\text{MHz}$	–	470	–	pF



**Note:** Collector connected to heat sink.